



SI4154DY-T1-GE3 Information



For Reference Only

Part Number SI4154DY-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 40V 36A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI4154DY-T1-GE3 Specifications

Manufacturer Part Number SI4154DY-T1-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 36A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 105nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4230pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Ta), 7.8W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 36A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 40V MOSFET (Metal Oxide) 40V 40V 40V 40V 36A (Tc) 4.5V, 10V 4.5V, 10V 4.5V, 10V 4.5V @ 250μA 4230pF @ 20V 4230pF @ 20V 4230pF @ 20V 520V FET Feature - 50V Surface Mount Surface Mount	Series	TrenchFET?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C36A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs105nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4230pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.5W (Ta), 7.8W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature Supplier Device Package Package / Case 36A (Tc) 4.5V, 10V 3.5V (20V 4230pF @ 20V 4230pF @ 20	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs105nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4230pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.5W (Ta), 7.8W (Tc)Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 105nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4230pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Ta), 7.8W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	36A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4230pF @ 20V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5W (Ta), 7.8W (Tc) 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 4230pF @ 20V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Ta), 7.8W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	105nC @ 10V
FET Feature - Power Dissipation (Max) 3.5W (Ta), 7.8W (Tc) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	4230pF @ 20V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.3 mOhm @ 15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.3 mOhm @ 15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	3.5W (Ta), 7.8W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	3.3 mOhm @ 15A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4154DY-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4154DY-T1-GE3 Payment Methods





















SI4154DY-T1-GE3 Shipping Methods













If you have any question about SI4154DY-T1-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com